

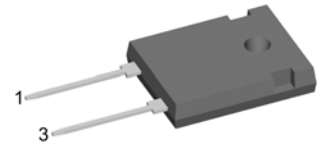
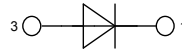
HiPerFRED²

High Performance Fast Recovery Diode
Low Loss and Soft Recovery
Single Diode

$V_{RRM} = 300\text{ V}$
 $I_{FAV} = 60\text{ A}$
 $t_{rr} = 35\text{ ns}$

Part number

DPG 60 I 300 HA



Backside: cathode

Features / Advantages:

- Planar passivated chips
- Very low leakage current
- Very short recovery time
- Improved thermal behaviour
- Very low I_{rm} -values
- Very soft recovery behaviour
- Avalanche voltage rated for reliable operation
- Soft reverse recovery for low EMI/RFI
- Low I_{rm} reduces:
 - Power dissipation within the diode
 - Turn-on loss in the commutating switch

Applications:

- Antiparallel diode for high frequency switching devices
- Antisaturation diode
- Snubber diode
- Free wheeling diode
- Rectifiers in switch mode power supplies (SMPS)
- Uninterruptible power supplies (UPS)

Package:

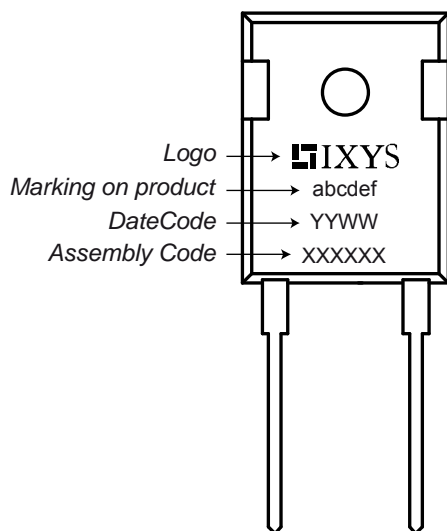
- Housing: TO-247
- Industry standard outline
- Epoxy meets UL 94V-0
- RoHS compliant

Ratings

Symbol	Definition	Conditions	Ratings			Unit	
			min.	typ.	max.		
V_{RRM}	max. repetitive reverse voltage				300	V	
I_R	reverse current	$V_R = 300\text{ V}$			1	μA	
		$V_R = 300\text{ V}$			0.35	mA	
V_F	forward voltage	$I_F = 60\text{ A}$			1.40	V	
		$I_F = 120\text{ A}$			1.72	V	
		$I_F = 60\text{ A}$	$T_{VJ} = 150^\circ\text{C}$			1.10	V
		$I_F = 120\text{ A}$	$T_{VJ} = 150^\circ\text{C}$			1.45	V
I_{FAV}	average forward current	rectangular $d = 0.5$	$T_C = 125^\circ\text{C}$		60	A	
V_{F0}	threshold voltage	} for power loss calculation only	$T_{VJ} = 175^\circ\text{C}$		0.69	V	
r_F	slope resistance				5.8	m Ω	
R_{thJC}	thermal resistance junction to case				0.55	K/W	
T_{VJ}	virtual junction temperature		-55		175	$^\circ\text{C}$	
P_{tot}	total power dissipation		$T_C = 25^\circ\text{C}$		275	W	
I_{FSM}	max. forward surge current	$t = 10\text{ ms}$ (50 Hz), sine	$T_{VJ} = 45^\circ\text{C}$		450	A	
I_{RM}	max. reverse recovery current		$T_{VJ} = 25^\circ\text{C}$		3.5	A	
		$I_F = 60\text{ A}; V_R = 150\text{ V}$	$T_{VJ} = 125^\circ\text{C}$		9	A	
t_{rr}	reverse recovery time	$-di_F/dt = 200\text{ A}/\mu\text{s}$	$T_{VJ} = 25^\circ\text{C}$		35	ns	
			$T_{VJ} = 125^\circ\text{C}$		65	ns	
C_J	junction capacitance	$V_R = 150\text{ V}; f = 1\text{ MHz}$	$T_{VJ} = 25^\circ\text{C}$		80	pF	

Symbol	Definition	Conditions	Ratings			Unit
			min.	typ.	max.	
I_{RMS}	RMS current	per pin ¹⁾			70	A
R_{thCH}	thermal resistance case to heatsink			0.25		K/W
T_{stg}	storage temperature		-55		150	°C
Weight				6		g
M_D	mounting torque		0.8		1.2	Nm
F_C	mounting force with clip		20		120	N

¹⁾ I_{RMS} is typically limited by: 1. pin-to-chip resistance; or by 2. current capability of the chip.
 In case of 1, a common cathode/anode configuration and a non-isolated backside, the whole current capability can be used by connecting the backside.

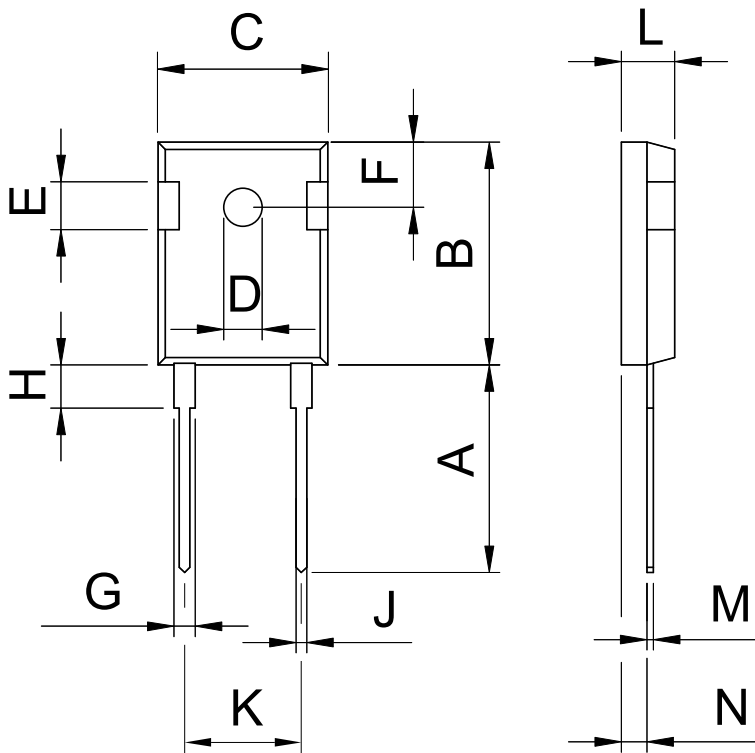
Product Marking

Part number

- D = Diode
- P = HiPerFRED
- G = extreme fast
- 60 = Current Rating [A]
- I = Single Diode
- 300 = Reverse Voltage [V]
- HA = TO-247AD (2)

Ordering	Part Name	Marking on Product	Delivering Mode	Base Qty	Code Key
Standard	DPG 60 I 300 HA	DPG60I300HA	Tube	30	585818

Similar Part	Package	Voltage Class
DPG60IM300PC	TO-263AB (D2Pak)	300

Outlines TO-247



Dim.	Millimeter		Inches	
	Min.	Max.	Min.	Max.
A	19.81	20.32	0.780	0.800
B	20.80	21.46	0.819	0.845
C	15.75	16.26	0.610	0.640
D	3.55	3.65	0.140	0.144
E	4.32	5.49	0.170	0.216
F	5.4	6.2	0.212	0.244
G	1.65	2.13	0.065	0.084
H	-	4.5	-	0.177
J	1.0	1.4	0.040	0.055
K	10.8	11.0	0.426	0.433
L	4.7	5.3	0.185	0.209
M	0.4	0.8	0.016	0.031
N	1.5	2.49	0.087	0.102

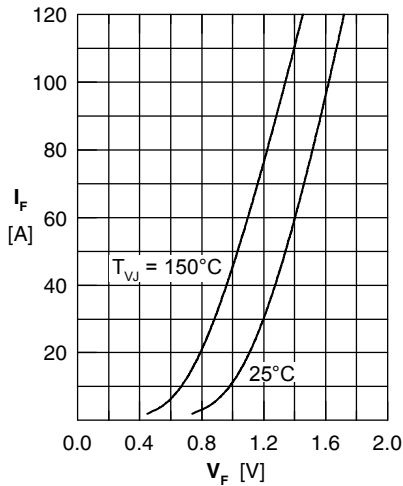


Fig. 1 Forward current I_F versus forward voltage V_F

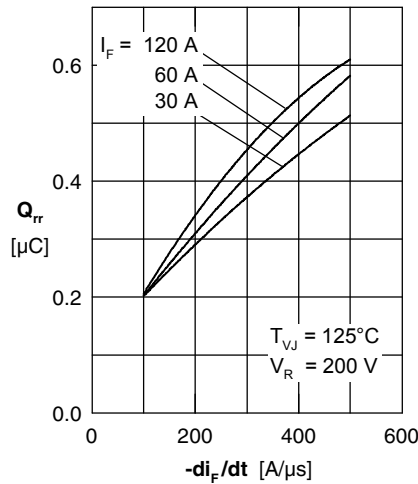


Fig. 2 Typ. reverse recovery charge Q_{rr} versus $-di_F/dt$

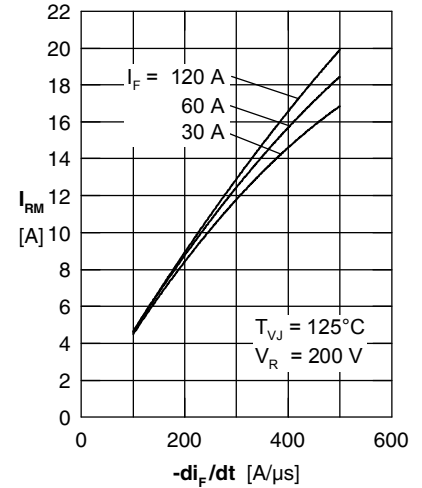


Fig. 3 Typ. reverse recovery current I_{RM} versus $-di_F/dt$

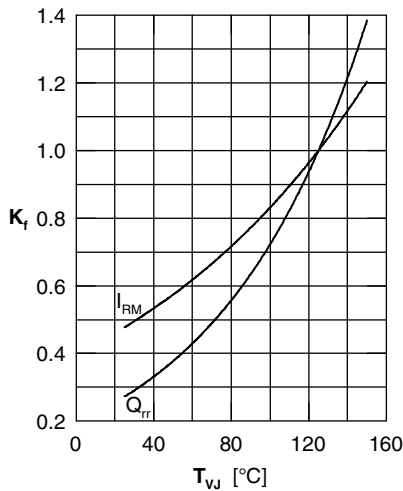


Fig. 4 Dynamic parameters Q_{rr} , I_{RM} versus T_{VJ}

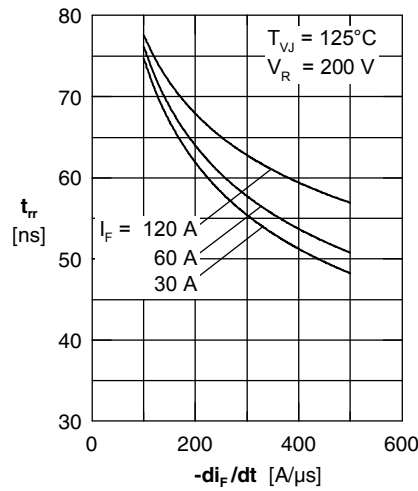


Fig. 5 Typ. reverse recovery time t_{rr} versus $-di_F/dt$

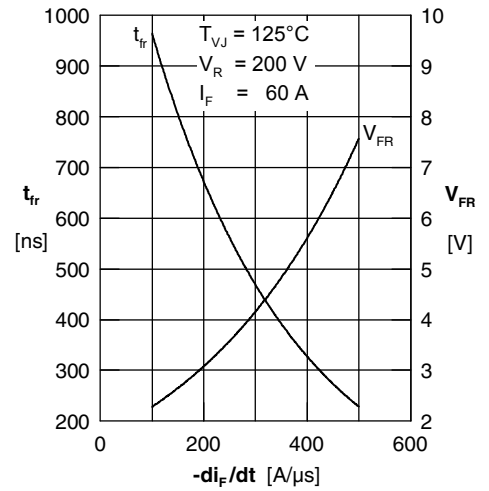


Fig. 6 Typ. forward recovery voltage V_{FR} & forward recovery time t_{fr} vs. di_F/dt

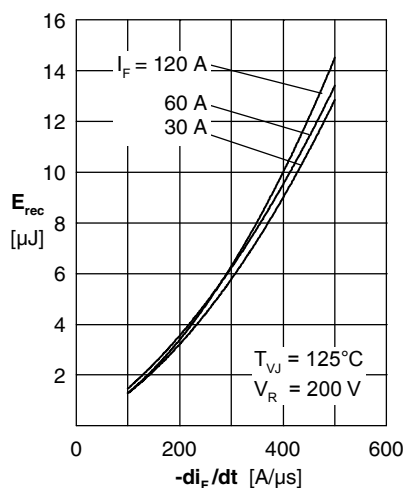


Fig. 7 Typ. recovery energy E_{rec} versus $-di_F/dt$

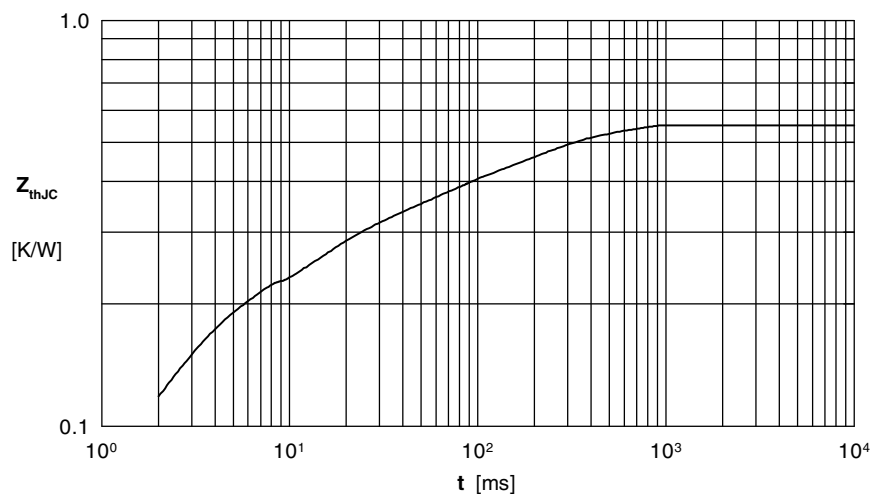


Fig. 8 Transient thermal impedance junction to case